

Serial No.: 10/044,493

places the application in a better condition for allowance and/or appeal. Accordingly, entry of the reply is considered proper.

Favorable reconsideration of the application is respectfully requested in view of the following.

IN THE CLAIMS:

Please place claim 20 in independent form as follows. A marked version of the amended claim appears in Appendix A attached hereto.

20. (amended) A semiconductor device comprising:
 - a source and a drain, said source and drain consisting essentially of silicide;
 - a semiconductor body disposed between the source and the drain, wherein a source/body junction is defined by silicide material of the source and semiconductor material of the body and a drain/body junction is defined by silicide material of the drain and semiconductor material of the body;
 - a gate electrode disposed over the body and defining a channel interposed between the source and the drain; and
 - a gate dielectric made from a high-K material and separating the gate electrode and the body.